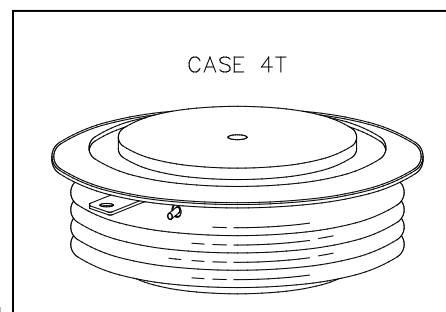


HIGH POWER THYRISTOR FOR PHASE CONTROL APPLICATIONS

R395CH21

Features:

- . All Diffused Structure
- . Center Amplifying Gate Configuration
- . Blocking capability up to 2100 volts
- . Guaranteed Maximum Turn-Off Time
- . High dV/dt Capability
- . Pressure Assembled Device



ELECTRICAL CHARACTERISTICS AND RATINGS

Blocking - Off State

V_{RRM} (1)	V_{DRM} (1)	V_{RSM} (1)
2100	2100	2200

V_{RRM} = Repetitive peak reverse voltage

V_{DRM} = Repetitive peak off state voltage

V_{RSM} = Non repetitive peak reverse voltage (2)

Repetitive peak reverse leakage and off state	I_{RRM} / I_{DRM}	30 mA 150 mA (3)
Critical rate of voltage rise	dV/dt (4)	200 V/μsec

Notes:

All ratings are specified for $T_j = 25^\circ\text{C}$ unless otherwise stated.

(1) All voltage ratings are specified for an applied 50Hz/60Hz sinusoidal waveform over the temperature range -40 to $+125^\circ\text{C}$.

(2) 10 msec. max. pulse width

(3) Maximum value for $T_j = 125^\circ\text{C}$.

(4) Minimum value for linear and exponential waveshape to 80% rated V_{DRM} . Gate open. $T_j = 125^\circ\text{C}$.

(5) Non-repetitive value.

(6) The value of di/dt is established in accordance with EIA/NIMA Standard RS-397, Section 5-2-2-6. The value defined would be in addition to that obtained from a snubber circuit, comprising a 0.2 μF capacitor and 20 ohms resistance in parallel with the thristor under test.

Conducting - on state

Parameter	Symbol	Min.	Max.	Typ.	Units	Conditions
Average value of on-state current	$I_{T(AV)}$		1275		A	Sinewave, 180° conduction, $T_c = 80^\circ\text{C}$
RMS value of on-state current	I_{TRMS}		1570		A	Nominal value
Peak one cycle surge (non repetitive) current	I_{TSM}		15500		A	8.3 msec (60Hz), sinusoidal wave-shape, 180° conduction, $T_j = 125^\circ\text{C}$
					A	10.0 msec (50Hz), sinusoidal wave-shape, 180° conduction, $T_j = 125^\circ\text{C}$
I square t	I^2t		1.2×10^6		A^2s	8.3 msec and 10.0 msec
Latching current	I_L		1000		mA	$V_D = 24\text{ V}$; $R_L = 12\text{ ohms}$
Holding current	I_H		500		mA	$V_D = 24\text{ V}$; $I = 2.5\text{ A}$
Peak on-state voltage	V_{TM}		1.9		V	$I_{TM} = 2000\text{ A}$; Duty Cycle $\leq 0.01\%$; $T_j = 125^\circ\text{C}$

Critical rate of rise of on-state current (5, 6)	di/dt		200		A/ μ s	Switching from $V_{DRM} \leq 1000$ V, non-repetitive
Critical rate of rise of on-state current (6)	di/dt		100		A/ μ s	Switching from $V_{DRM} \leq 1000$ V

ELECTRICAL CHARACTERISTICS AND RATINGS

Gating

Parameter	Symbol	Min.	Max.	Typ.	Units	Conditions
Peak gate power dissipation	P_{GM}		200		W	$t_p = 40$ μ s
Average gate power dissipation	$P_{G(AV)}$		5		W	
Peak gate current	I_{GM}		10		A	
Gate current required to trigger all units	I_{GT}		- 150 -		mA mA mA	$V_D = 6$ V; $R_L = 3$ ohms; $T_j = -40$ °C $V_D = 6$ V; $R_L = 3$ ohms; $T_j = +25$ °C $V_D = 6$ V; $R_L = 3$ ohms; $T_j = +125$ °C
Gate voltage required to trigger all units	V_{GT}		- 3.0 -		V V V	$V_D = 6$ V; $R_L = 3$ ohms; $T_j = -40$ °C $V_D = 6$ V; $R_L = 3$ ohms; $T_j = 0-125$ °C $V_D = \text{Rated } V_{DRM}$; $R_L = 1000$ ohms; $T_j = +125$ °C
Peak negative voltage	V_{GRM}		5		V	

Dynamic

Parameter	Symbol	Min.	Max.	Typ.	Units	Conditions
Delay time	t_d		1.5	0.7	μ s	$I_{TM} = 50$ A; $V_D = \text{Rated } V_{DRM}$ Gate pulse: $V_G = 20$ V; $R_G = 20$ ohms; $t_r = 0.1$ μ s; $t_p = 20$ μ s
Turn-off time (with $V_R = -50$ V)	t_q		-	60	μ s	$I_{TM} = 1000$ A; di/dt = 25 A/ μ s; $V_R \geq -50$ V; Re-applied dV/dt = 20 V/ μ s linear to 80% V_{DRM} ; $V_G = 0$; $T_j = 125$ °C; Duty cPSTcle $\geq 0.01\%$
Reverse recovery charge	Q_{rr}		*		μ C	$I_{TM} = 1000$ A; di/dt = 25 A/ μ s; $V_R \geq -50$ V

* For guaranteed max. value, contact factory.

THERMAL AND MECHANICAL CHARACTERISTICS AND RATINGS

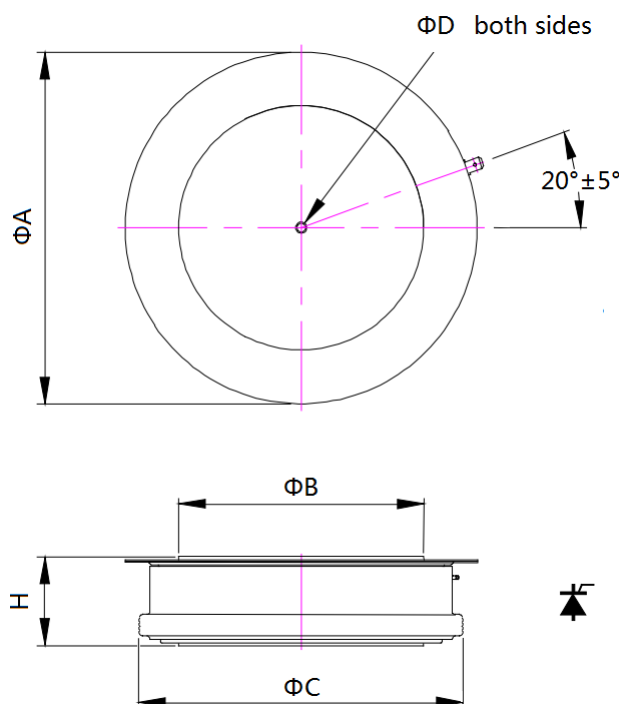
Parameter	Symbol	Min.	Max.	Typ.	Units	Conditions
Operating temperature	T_j	-40	+125		°C	
Storage temperature	T_{stg}	-40	+125		°C	
Thermal resistance - junction to case	$R_{\theta(j-c)}$		0.024		°C/W	Double sided cooled

			0.048			Single sided cooled
Thermal resistance - case to sink	$R_{\Theta (c-s)}$		-		°C/W	Double sided cooled * Single sided cooled *
Mounting force	P	19	26.7		kN	
Weight	W			460	g	About

* Mounting surfaces smooth, flat and greased

Note : for case outline and dimensions, see case outline drawing in last page of this Technical Data

CASE OUTLINE AND DIMENSIONS



Sym	A	B	C	D	H
mm	75	47	66	3.5×3	26±1